

[查询TM25EZ-24供应商](#)

[捷多邦, 专业PCB打样工厂, 24小时加急出货](#)

MITSUBISHI THYRISTOR MODULES

TM25RZ/EZ-24,-2H

HIGH VOLTAGE MEDIUM POWER GENERAL USE
INSULATED TYPE

TM25RZ/EZ-24,-2H



- **IT (AV)** Average on-state current **25A**
- **IF (AV)** Average forward current **25A**
- **VRRM** Repetitive peak reverse voltage
..... **1200/1600V**
- **VDRM** Repetitive peak off-state voltage
..... **1200/1600V**
- **MIX DOUBLE ARMS**
- **Insulated Type**
- **UL Recognized**

Yellow Card No. E80276 (N)

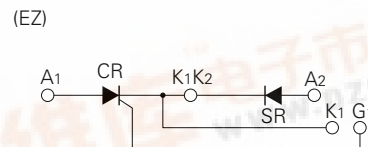
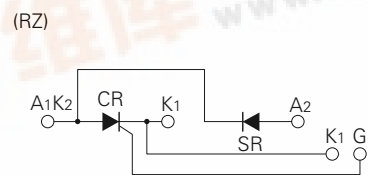
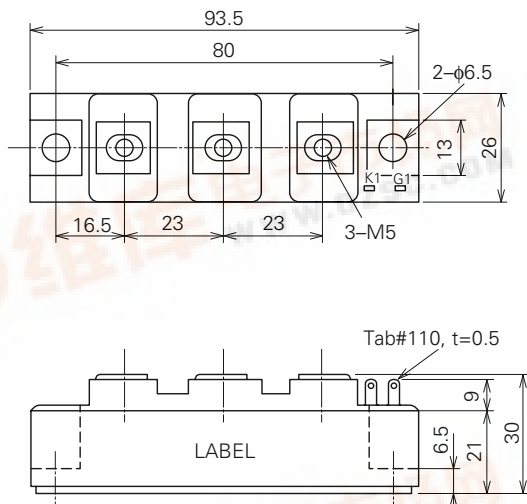
File No. E80271

APPLICATION

DC motor control, NC equipment, AC motor control, contactless switches,
electric furnace temperature control, light dimmers

OUTLINE DRAWING & CIRCUIT DIAGRAM

Dimensions in mm



TM25RZ/EZ-24,-2H

**HIGH VOLTAGE MEDIUM POWER GENERAL USE
INSULATED TYPE**

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Voltage class		Unit
		24	H	
VRRM	Repetitive peak reverse voltage	1200	1600	V
VRSM	Non-repetitive peak reverse voltage	1350	1700	V
VR (DC)	DC reverse voltage	960	1280	V
VDRM	Repetitive peak off-state voltage	1200	1600	V
VDSM	Non-repetitive peak off-state voltage	1350	1700	V
VD (DC)	DC off-state voltage	960	1280	V

Symbol	Parameter	Conditions	Ratings	Unit
IT (RMS), IF (RMS)	RMS current		39	A
IT (AV), IF (AV)	Average current	Single-phase, half-wave 180° conduction, Tc=87°C	25	A
ITSM, IFSM	Surge (non-repetitive) current	One half cycle at 60Hz, peak value	500	A
I ² t	I ² t for fusing	Value for one cycle of surge current	1.0 × 10 ³	A ² s
di/dt	Critical rate of rise of on-state current	V _D =1/2V _{DRM} , I _G =1.0A, T _j =125°C	100	A/μs
PGM	Peak gate power dissipation		5.0	W
PG (AV)	Average gate power dissipation		0.5	W
VFGM	Peak gate forward voltage		10	V
VRGM	Peak gate reverse voltage		5.0	V
IFGM	Peak gate forward current		2.0	A
T _j	Junction temperature		-40~125	°C
T _{stg}	Storage temperature		-40~125	°C
Viso	Isolation voltage	Charged part to case	2500	V
—	Mounting torque	Main terminal screw M5	1.47~1.96	N·m
			15~20	kg·cm
		Mounting screw M6	1.96~2.94	N·m
			20~30	kg·cm
—	Weight	Typical value	160	g

ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
I _{RRM}	Repetitive peak reverse current	T _j =125°C, V _{RRM} applied	—	—	10	mA
I _{DRM}	Repetitive peak off-state current	T _j =125°C, V _{DRM} applied	—	—	10	mA
V _{TM} , V _{FM}	Forward voltage	T _j =125°C, I _{TM} =I _{FM} =75A, instantaneous meas.	—	—	1.8	V
dv/dt	Critical rate of rise of off-state voltage	T _j =125°C, V _D =2/3V _{DRM}	500	—	—	V/μs
V _{GT}	Gate trigger voltage	T _j =25°C, V _D =6V, R _L =2Ω	—	—	3.0	V
V _{GD}	Gate non-trigger voltage	T _j =125°C, V _D =1/2V _{DRM}	0.25	—	—	V
I _{GT}	Gate trigger current	T _j =25°C, V _D =6V, R _L =2Ω	10	—	50	mA
R _{th (j-c)}	Thermal resistance	Junction to case (per 1/2 module)	—	—	0.8	°C/W
R _{th (c-f)}	Contact thermal resistance	Case to fin, conductive grease applied (per 1/2 module)	—	—	0.20	°C/W
—	Insulation resistance	Measured with a 500V megohmmeter between main terminal and case	10	—	—	MΩ

Note: Items of the above table applies to the Thyristor part and the Diode part as circled in the following tables.

TM25RZ/EZ-24,-2H

HIGH VOLTAGE MEDIUM POWER GENERAL USE
INSULATED TYPE

MAXIMUM RATINGS

Item	VRRM	VRSM	VR (DC)	VDRM	VDSM	VD (DC)	IT (RMS)	IT (AV)	ITSM	I^2t	di/dt
							IF (RMS)	IF (AV)	IFSM		
Thyristor	○	○	○	○	○	○	○	○	○	○	○
Diode	○	○	○	—	—	—	○	○	○	○	—

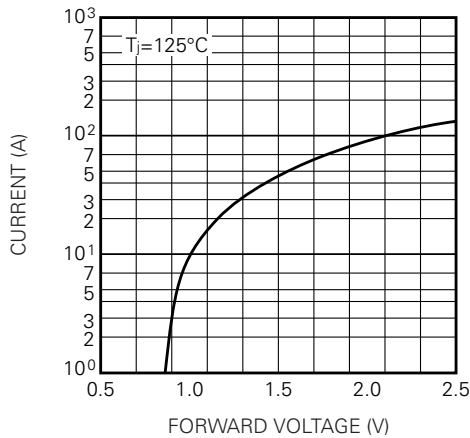
Item	PGM	PG (AV)	VFGM	IFGM	T _j	T _{stg}
Thyristor	○	○	○	○	○	○
Diode	—	—	—	—	○	○

ELECTRICAL CHARACTERISTICS

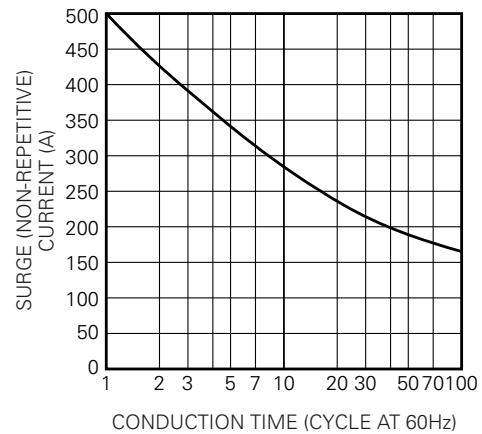
Item	IRRM	IDRM	VTM	dv/dt	VGT	VGD	IGT	Rth (j-c)	Rth (c-f)
			VFM						
Thyristor	○	○	○	○	○	○	○	○	○
Diode	○	—	○	—	—	—	—	○	○

PERFORMANCE CURVES

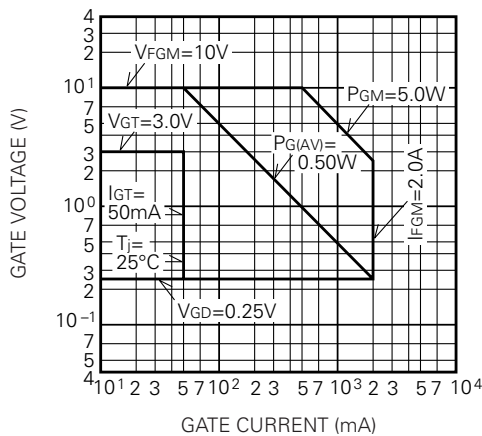
MAXIMUM FORWARD CHARACTERISTIC



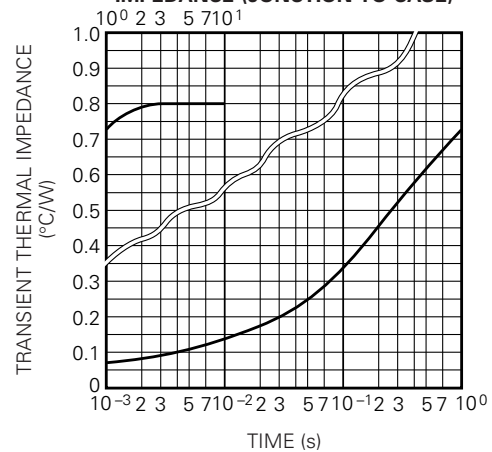
RATED SURGE (NON-REPETITIVE) CURRENT



GATE CHARACTERISTICS



MAXIMUM TRANSIENT THERMAL IMPEDANCE (JUNCTION TO CASE)



TM25RZ/EZ-24,-2H

HIGH VOLTAGE MEDIUM POWER GENERAL USE
INSULATED TYPE

